Electronic Supplementary Material (ESI) for Nanoscale.

Towards parallel fabrication single electron transistors using carbon nanotubes

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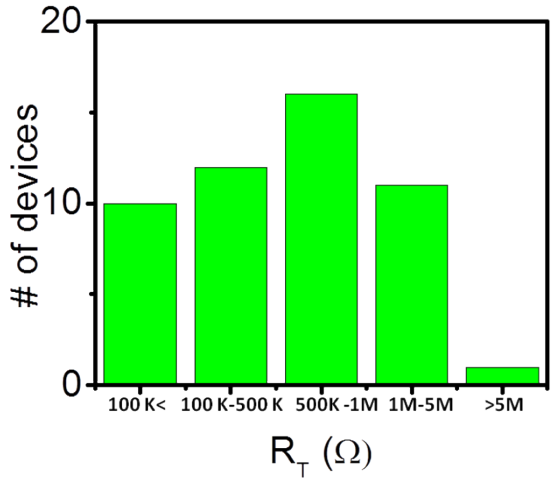
Supplementary figure S1: Figure S1 demonstrates the variation of room temperature resistance of 50 SET devices.



S1. Variation of room temperature resistance of the 100 nm metal-SWNT devices

Supplementary table 1: A summary of the charging energy of the top contact devices as a function of R_T. From the electron transport measurements of 50 top contact devices we found that most (~90%) of the devices with 100 kΩ < R_T < 1 MΩ shows single QD behavior with consistent charging energy (~ 15 ± 5 meV). Multiple QD behavior with high charging energy (between 15-200 meV) is observed for the devices with R_T > 1MΩ.

Table 1. Summary of the SET devices

R_T	# of Devices measured	SET observed
R_T <100 kΩ	10	1
100 kΩ <R_T <1MΩ	28	25
R_T > 1 MΩ	12	12